

INFORMATION DISCLOSURE CITATION				ATTORNEY'S DKT NO. 025219-382		APPLICATION NO. Unassigned	
PTO-1449				APPLICANT Bernard Aspar, et al.		GROUP Unassigned	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
W	5,256,581	10/26/93	Foerstner, et. al.	437	24		
W	5,374,564	12/20/94	Bruehl	437	24		
W	5,783,477	07/21/98	Kish, Jr. et. al.	438	455		
W	5,953,622	09/14/99	Lee, et al.	438	458		
W	5,993,677	11/30/99	Biasse, et al.	216	36		
W	6,013,563	01/11/00	Henley, et al.	438	458		
W	6,020,252	02/01/00	Aspar, et al.	438	458		
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
W	2 758 907	07/31/98	France				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
W	Hiroshi Wada, et al.: "Electrical Characteristics Of Directly-Bonded GaAs and InP" Applied Physics Letters, vol. 62, no. 7, 15 February 1993, pages 738-740, XP000338292						
EXAMINER				DATE CONSIDERED			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.